

ABSTRACT OF THE DISCLOSURE

The present invention provides a method of manufacturing a semiconductor device which includes a step of forming a laminated film for pattern formation on a substrate, in which the laminated film for pattern formation includes an innermost layer, an inner layer and a surface layer, an extinction coefficient k of the innermost layer is 0.3 or more, and an extinction coefficient k of the inner layer is 0.12 or more. It also provides a method of forming a pattern which includes a step of forming a laminated film for pattern formation on a substrate, in which the laminated film for pattern formation includes an innermost layer, an inner layer and a surface layer, an extinction coefficient k of the innermost layer is 0.3 or more, and an extinction coefficient k of the inner layer is 0.12 or more.